

A Hybrid $\text{Al}_{0.10}\text{Ga}_{0.90}\text{As}/\text{AlAs}$ Bilayer Electron System

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(Dated: April 14, 2024)

We have fabricated a device composed of two closely coupled two-dimensional electron systems, one of which resides within an AlAs quantum well (QW) at the X point of the Brillouin zone (BZ), while the other is contained at the Γ point of the BZ in the alloy $\text{Al}_{0.10}\text{Ga}_{0.90}\text{As}$, grown directly below the AlAs QW. The electronic properties of these two systems are strongly asymmetric: the respective cyclotron masses in the AlAs and the $\text{Al}_{0.10}\text{Ga}_{0.90}\text{As}$ layers, measured in units of the free electron mass, are 0.46 and 0.07, while the effective electron g -factors are approximately 8.5 and 0. With the help of front and back gates, we can confine mobile carriers to either or both of the two QWs, as confirmed by magnetotransport measurements.

In their approach to building a logic gate for quantum computing, DiVincenzo et al. [1] have proposed a device in which the quantum information unit (or qubit) is encoded in the electron spin, which can be reversed by electrically shifting the electron from a material with a low effective g -factor (g) to a high- g material in a magnetic field. The advantage of this design lies in the fact that the spin coherence time is typically longer than that of the spatial component of the electron wavefunction; furthermore, the above design is in principle compatible with existing semiconductor fabrication techniques.

Several groups have begun to implement DiVincenzo's scheme [2, 3, 4]: in all of these cases, the electron system is excited optically, and contained primarily in one quantum well (QW). By contrast, the structure we present in this work is composed of two separate QWs, made out of AlAs and $\text{Al}_{0.10}\text{Ga}_{0.90}\text{As}$. Charge carriers in these QWs lie respectively at the X and Γ points of the Brillouin zone, at nearly identical conduction band energies (E_c). This structure is therefore a direct implementation of DiVincenzo's scheme [1]. We show through magnetoresistance measurements that electrons in these two QWs possess different g -factors: 8.5 and 0, respectively. Furthermore, the cyclotron effective masses (m) of two-dimensional (2D) electrons in AlAs and $\text{Al}_{0.10}\text{Ga}_{0.90}\text{As}$ are 0.46 and 0.07, respectively [5, 6]. Our structure therefore allows to study the properties of bilayer electron systems with unequal masses. We also note that the X and Γ character of 2D electrons in the two QW materials strongly suppresses tunnelling between the two 2D electron layers [7].

Our sample was grown by molecular beam epitaxy (MBE) on a GaAs (100) substrate wafer. The structure of the epitaxial growth is given in Fig. 1(b), and contains a 15 nm-wide AlAs QW grown atop a 25 nm-wide $\text{Al}_{0.10}\text{Ga}_{0.90}\text{As}$ QW. Both QWs are bordered by $\text{Al}_{0.39}\text{Ga}_{0.61}\text{As}$ barriers, and the $\text{Al}_{0.10}\text{Ga}_{0.90}\text{As}$ layer was constructed as a 10 (1.85 nm $\text{GaAs}/0.65$ nm $\text{Al}_{0.39}\text{Ga}_{0.61}\text{As}$) superlattice. For modulation doping, Si-layers were inserted within the barriers, separated from the QWs by 40 nm- and 55 nm-wide spacers on the front and back sides, respectively. We designed the

structure so as to align the X and Γ E_c 's of the AlAs and $\text{Al}_{0.10}\text{Ga}_{0.90}\text{As}$ QWs, respectively [8], as can be seen in the band diagram of Fig. 1(c). We note that only the in-plane X valleys of the AlAs QW are occupied in our sample, in spite of their higher out-of-plane effective mass, as the small stress resulting from the AlAs - GaAs lattice mismatch raises the energy of the out-of-plane valley [5, 9].

For magnetotransport measurements, samples were patterned as Hall bar mesas by optical lithography, and 140 nm-thick ohmic AuGeNi contacts were deposited and alloyed at 460 °C for 10 minutes in forming gas. A semi-transparent, 30 nm-thick, Ti/Au metal layer deposited on the surface of each sample served as a front gate, and an In-covered Si chip was soldered to the back of the sample for back gate biasing. Transport measurements were performed in a pumped ^3He system at $T = 0.3\text{K}$ and in magnetic fields up to 12 T.

In Fig. 2(a) and (b) we plot the longitudinal magnetoresistance (R_{xx}) of the sample, measured as a function of the perpendicular magnetic field, for different front- and back-gate biases (V_{FG} and V_{BG} , respectively). For the traces shown in Fig. 2(a), V_{FG} and V_{BG} are such that electrons populate the $\text{Al}_{0.10}\text{Ga}_{0.90}\text{As}$ QW only ("AlGaAs regime"). A side from an R_{xx} minimum at Landau level filling $\nu_{\text{AlGaAs}} = 1$ [10], R_{xx} minima are strong for even filling factors only. This behavior is expected for $\text{Al}_{0.10}\text{Ga}_{0.90}\text{As}$ 2D electrons, for which $g = 0$ [11]. In Fig. 2(b), the 2D electron density in the $\text{Al}_{0.10}\text{Ga}_{0.90}\text{As}$ QW has been reduced to $1.9 \times 10^{11} \text{ cm}^{-2}$ by application of a large negative $V_{BG} = -500 \text{ V}$. In this state, increasing V_{FG} acts to raise the carrier density in the AlAs QW ("AlAs regime"). The minima observed in the R_{xx} data all correspond to integer Landau level fillings of the AlAs 2D electrons (both even and odd ν 's are apparent). Furthermore, the data in this regime look highly similar to those measured in single AlAs QWs of comparable quality [5]. R_{xx} data in Fig. 2(b) also show that for $V_{FG} > 150 \text{ mV}$, a large fraction of the 10 nA current driven through the sample passes through the AlAs QW, as none of the R_{xx} oscillations in Fig. 2(b) can be associated with the AlGaAs 2D electrons.

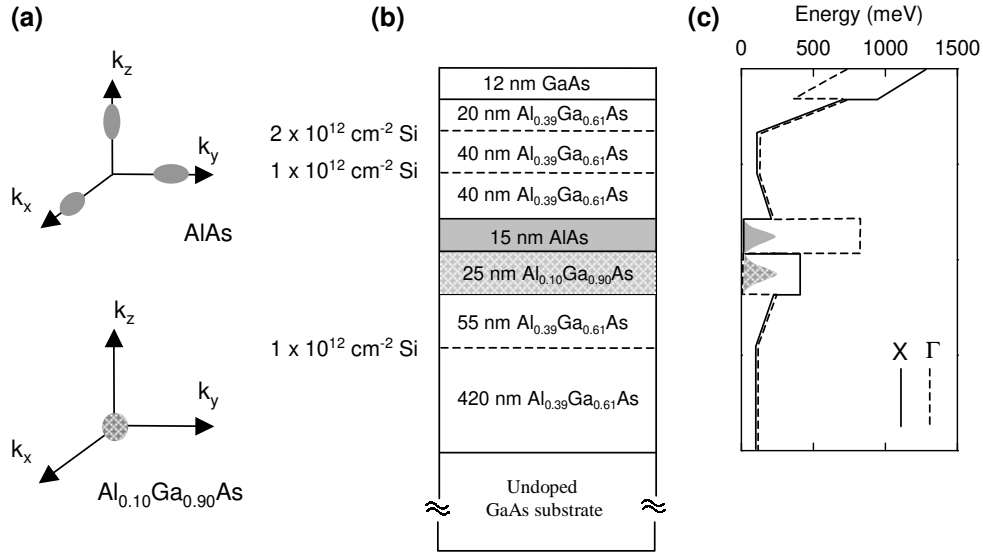


FIG. 1: (a) Fermi surfaces of conduction electrons in bulk AlAs and Al_{0.10}Ga_{0.90}As. (b) Layer structure of the bilayer sample. (c) Schematic conduction band diagram of the sample; X-point and Γ -point conduction band edges are indicated by solid and dashed lines, respectively. The sample is designed so as to align the conduction band minima of the AlAs and AlGaAs QWs (at the X and Γ points, respectively). Note that each QW acts as a potential barrier for electrons in the other well.

As further evidence that both the Al_{0.10}Ga_{0.90}As and AlAs QWs can be occupied with charge carriers, we measure the effective g of the bilayer system for two different sets of front- and back-gate biases, corresponding to the highlighted data in Fig. 2 (a) and (b). We derive g using the coincidence method [12]: in this technique, the sample is placed at an angle with respect to the direction of the B field (Fig. 2 (c), inset). For particular values, the Zeeman energy, $E_Z = g_B B$ (where B is the Bohr magneton), is an integer multiple of the cyclotron energy, equal to $\hbar e B / m_e$ (B is the perpendicular component of B and m_e is the bare electron mass): these two energies depend on the total and perpendicular magnetic field, respectively, whose ratio is controlled by $\cos \theta$. In these conditions, the energy ladders of spin-up and spin-down Landau levels overlap, resulting in the weakening of even (or odd) R_{xx} quantum Hall minima. In our case, the value of θ for which the R_{xx} minima disappear or become weakest is related to g and to m via the formula $g m = 4 \cos \theta$ [13].

We concentrate on the two highlighted traces in Fig. 2 (a) and (b). For each of these states, we then measure $R_{xx}(B)$ for different θ , as plotted in Fig. 2 (c) and (d). In the first case, the R_{xx} data is insensitive to θ , showing that $g m \approx 0$. In the latter case [Fig. 2 (d)], Landau level coincidences occur for $\theta = 14^\circ, 53^\circ$, and 63° , yielding $g m = 3.9$. The measured g are therefore ≈ 0 in the former case, and 8.5 in the latter (taking $m = 0.46$ [5]). $g \approx 0$ is the value expected for Al_xGa_{1-x}As 2D electrons with $x = 0.10$ [11], while $g = 8.5$ is close to the value previously obtained for AlAs 2D electrons [13]. These measurements confirm that the R_{xx} data in the up-

per panels of Fig. 2 describe Al_{0.10}Ga_{0.90}As 2D electrons, while the lower panels of the same figure correspond to AlAs 2D electrons.

Additionally, the Dingle plot of Fig. 3, obtained from the temperature dependence of the Shubnikov-de Haas oscillations of the $V_{FG} = 100$ mV data in Fig. 2 (a), yields $m^* = 0.07$, the effective mass expected for Al_{0.10}Ga_{0.90}As electrons. Our Dingle data in the AlAs regime are so far harder to interpret, but yield a range of effective masses all somewhat larger than ≈ 0.5 , also consistent with the 2D electron mass in AlAs.

We conclude with practical considerations on sample fabrication. Samples similar to the one we have described require a precise alignment between the electron energy levels in AlAs and Al_{0.10}Ga_{0.90}As, and thus demand: (1) knowledge of the conduction band offsets between the two materials and (2) good control over Al and Ga fluxes during epitaxial growth. Such control is difficult but possible to achieve in practice. In our case, since we do not rotate the wafer during MBE growth, we have a flux inhomogeneity of about 15% across the two-inch wafer. This spatial variation results in a slow variation of the QW thickness and of the Al concentration gradient within the Al_{0.10}Ga_{0.90}As QW across the wafer, and increases the likelihood that in some section of the wafer both QWs will be occupied. With this technique, we have so far obtained four other samples (from three different wafers) similar to the one presented in this article. We add that present day MBE technology makes it possible to grow very uniform and homogeneous wafers with precise composition and thicknesses. Using our sample parameters (Fig. 1) as a starting point, and by rotating the wafer

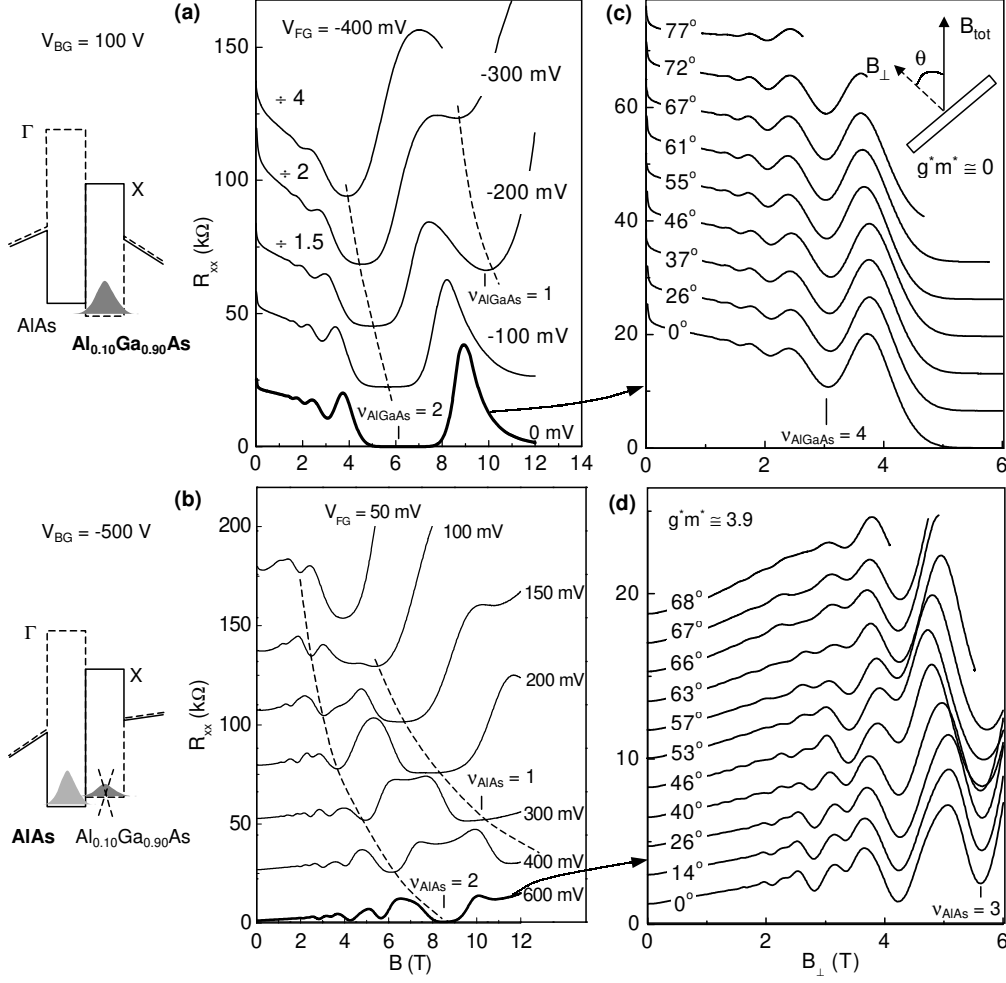


FIG. 2: Magnetoresistance of 2D electrons in the AlAs/Al_{0.10}Ga_{0.90}As bilayer sample (traces are offset vertically for clarity). In (a), $V_{BG} = 100$ V, and the front gate bias ranges from -400 to 0 mV, values for which only the back QW (Al_{0.10}Ga_{0.90}As) is occupied. Its density varies from 1.9 to $3.0 \times 10^{11} \text{ cm}^{-2}$. In (b), both QWs are filled, although most of the R_{xx} minimum arises from transport through the AlAs layer. In this case, the 2D electron density in the Al_{0.10}Ga_{0.90}As QW is $1.9 \times 10^{11} \text{ cm}^{-2}$, while in the AlAs QW, the density ranges from 1.0 to $4.1 \times 10^{11} \text{ cm}^{-2}$. (c) and (d): Tilted-field R_{xx} data for two different gate biases, corresponding to the highlighted traces in (a) and (b), respectively. R_{xx} does not vary with tilt angle in (c) ($g^*m^* \approx 0$), while in (d), several coincidences occur ($g^*m^* \approx 8.5$). g^* derived from these data are consistent with electron transport occurring through the Al_{0.10}Ga_{0.90}As layer in (c), and the AlAs layer in (d).

during MBE growth, it should be possible to grow wafers that contain larger areas of useful samples.

In summary, we have fabricated a new type of modulation-doped heterostructure, in which two 2D electron systems reside side-by-side in two different materials, AlAs and Al_{0.10}Ga_{0.90}As, with widely different effective g -factors and masses [14]. This structure allows to modulate electrostatically the g -factor of 2D carriers from a vanishingly small to a large value, and offers the first step towards the realization of a spin-based quantum computer. In addition, it constitutes a bilayer 2D system with near-zero tunnelling, but small separation between the component 2D electron gases, a system in which new electronic ground states may be observed. A supercon-

ducting transition has for example been predicted in such a two-mass bilayer 2D system [15].

This work is supported by the NSF and ARO.

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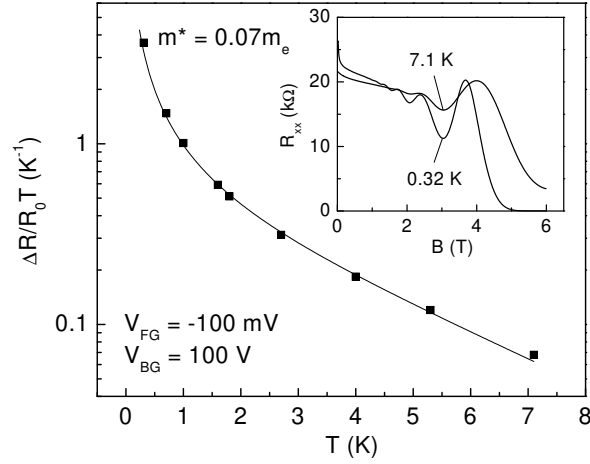


FIG. 3: Relative amplitude of the Shubnikov-de Haas magnetoresistance oscillations at $B = 3$ T plotted vs. T , and R_{xx} vs. B data (inset), for the state ($V_{FG} = -100$ mV) of Fig. 2(a). A fit to the Dingle formula yields $m^* = 0.07$, consistent with the effective mass of $Al_{0.10}Ga_{0.90}As$ 2D electrons.

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